

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: Li, *et al.* Attorney Docket: 2004 P 50199 US  
Filed: Herewith Examiner: TBD  
Serial No.: TBD Art Unit: TBD  
For: Transistor with Dopant-Bearing Metal in Source and Drain

Mail Stop: Patent Application  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

The Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08b that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Respectfully submitted,



Kay Houston  
Attorney for Applicants  
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March 18, 2004

Date

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				Application Number	TBD
				Filing Date	HEREWITH
				First Named Inventor	Li
				Art Unit	TBD
				Examiner Name	TBD
Sheet	1	of	1	Attorney Docket Number	2004 P 50199 US

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
	1	GANNAVARAM, S. <i>et al.</i> , "Low Temperature ( $\leq 800^{\circ}\text{C}$ ) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS," 0-7803-6441-4/00, IEEE/North Carolina State University, Raleigh, NC, 2000.		
	2	HUANG, F.J., <i>et al.</i> , "Schottky-Clamped NMOS Transistors Implemented in a Conventional 0.8- $\mu\text{m}$ CMOS Process," IEEE Electron Device Letters, September, 1998, pp. 326-328, Vol. 19, No. 9, IEEE, New York, NY.		
	3	"Front End Processes," International Technology Roadmap for Semiconductor (ITRS), 2002 Update, pp. 45-62, <a href="http://member.itrs.net/">http://member.itrs.net/</a> .		
	4	"Front End Processes," International Technology Roadmap for Semiconductor (ITRS), 2003 Edition, pp. 23-25, <a href="http://member.itrs.net/">http://member.itrs.net/</a> .		

Examiner Signature		Date Considered	
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